

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|--|---|---------------------|
| - | 83 | laser same anneal\$3 same (silicon or si) and 117/904.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 15:58 |
| - | 12 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma and ion near3 beam | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 16:58 |
| - | 78 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 16:05 |
| - | 41 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) and apparatus | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 16:25 |
| - | 15 | laser same (kev) same anneal\$3 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 16:58 |
| - | 5 | (CVD or chemical adj vapor adj deposition) same plasma and 117/98.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 17:01 |
| - | 19 | (CVD or chemical adj vapor adj deposition) same (si or silicon) and 117/98.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 17:03 |
| - | 51 | (CVD or chemical adj vapor adj deposition) same plasma same ion same beam and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 17:04 |
| - | 118 | ((CVD or chemical adj vapor adj deposition) same plasma) and 117/\$4.ccls. and ion near3 beam | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/05 17:09 |
| - | 63 | ((CVD or chemical adj vapor adj deposition) same plasma) same (silicon or si) and 117/\$4.ccls. and ion near3 beam | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/06 09:42 |
| - | 43 | (CVD or chemical adj vapor adj deposition) same (silicon or si) and 117/\$4.ccls. and ion near3 beam same (ar or argon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/06 10:19 |

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|---|---|---------------------|
| - | 76 | beam same (si or silicon) same (layer or film) same ion same amorphous and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/09 16:49 |
| - | 12 | CVD near3 ion same (si or silicon) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/09 16:53 |
| - | 109 | CVD same plasma same ion and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/09 17:02 |
| - | 68 | ion same (si or silicon) same (amorphous or seed or nucleus) same (beam or implant\$4) and 117/84-109.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 13:25 |
| - | 5 | ion same (si or silicon) same (amorphous or seed or nucleus) same (assist\$3) and 117/84-109.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 13:27 |
| - | 17 | ion same (si or silicon) same ECR and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 13:38 |
| - | 51 | (si or silicon) same (ECR or "electron cyclotron resonance") and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 13:40 |
| - | 19 | (si or silicon) same (ECR or "electron cyclotron resonance") same ion and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 14:58 |
| - | 82 | ion same substrate same (beam) same amorphous and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 15:16 |
| - | 14 | ion same substrate same (beam) same (si or silicon) same (nucle\$4) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 15:50 |
| - | 41 | ion same substrate same (si or silicon) same (nucle\$4) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 16:08 |
| - | 127 | ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 16:54 |
| - | 17 | ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) same ev and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 17:07 |

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| 9 | ion same (si or silicon) same amorphous same ev and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 17:10 |
| 6 | CVD same plasma same ev same (si or silicon) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 17:16 |
| 31 | CVD same plasma same (si or silicon) same energy and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 17:12 |
| 4 | CVD same plasma same kev same (si or silicon) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/10 17:16 |
| 73 | ion same (si or silicon) same amorphous same energy and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/11 09:45 |
| 83 | ion same (si or silicon) same amorphous same beam and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/11 10:08 |
| 81 | ion same (si or silicon) same polycrystal\$4 same beam and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/11 10:26 |
| 24 | ion same (si or silicon) same assist\$4 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/11 10:44 |
| 11 | plasma same cvd same ion same (kev or ev) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/11 11:11 |
| 38 | ion near2 beam same (kev or ev) same (si or silicon) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 11:31 |
| 21 | ion near2 beam same (kev or ev) same sputter\$3 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 13:23 |
| 32 | ion near2 beam same mov\$4 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 13:37 |
| 27 | ion same mov\$4 near4 substrate and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 14:06 |
| 59 | ion near3 beam same nucle\$5 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 16:37 |

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|---|-----|---|---|---------------------|
| - | 17 | ion near3 beam same seed\$3 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/12 16:45 |
| - | 17 | ion near3 beam same clean\$3 and mbe and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/12 17:06 |
| - | 21 | ion near3 beam same (oxide or native) and mbe and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/12 17:10 |
| - | 138 | ion same nucle\$4 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/13 09:22 |
| - | 43 | ion same substrate same (si or silicon) same beam same \$3treat\$4 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/13 09:50 |